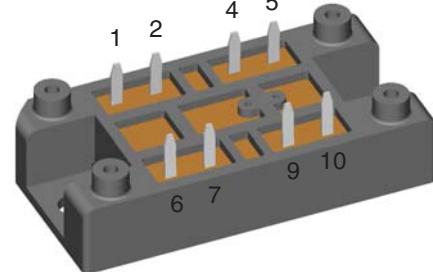
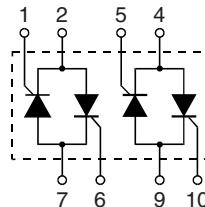


AC Controller Modules

I_{RMS} = 2x 60 A
V_{RRM} = 1200-1600 V

V _{RSM}	V _{RRM}	Type
V _{DSM}	V _{DRM}	
V V		
1200	1200	VW2x60-12io1
1400	1400	VW2x60-14io1
1600	1600	VW2x60-16io1



Symbol	Conditions	Maximum Ratings		
I _{RMS}	T _C = 85°C; 50 - 400 Hz (per phase)	60	A	
I _{TRMS}	T _{VJ} = T _{VJM}	43	A	
I _{TAVM}	T _C = 85°C; (180° sine)	27	A	
I _{TSM}	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	520	A
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	470	A
I ² t	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	510	A
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1350	A ² s
			1320	A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50 Hz, t _p = 200 µs V _D = 2/3 V _{DRM} I _G = 0.45 A di _G /dt = 0.45 A/µs	repetitive, I _T = 45 A	100	A/µs
		non repetitive, I _T = I _{TAVM}	500	A/µs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} R _{GK} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM}	1000	V/µs
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{TAVM}	t _p = 30 µs t _p = 300 µs	10 5	W W
P _{GAVM}			0.5	W
V _{RGM}			10	V
T _{VJ}			-40...+125	°C
T _{VJM}			125	°C
T _{stg}			-40...+125	°C
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	t = 1 min t = 1 s	3000 3600	V~
M _d	Mounting torque (M5)		2-2.5/18-22	Nm/lb.in.
Weight	typ.	35	g	

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.

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Symbol	Conditions	Characteristic Values			
I_D, I_R	$T_{VJ} = T_{VJM}$; $V_R = V_{RRM}$; $V_D = V_{DRM}$	\leq	5	mA	
V_T	$I_T = 80 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	\leq	1.65	V	
V_{TO}	For power-loss calculations only		0.85	V	
r_T			11	$\text{m}\Omega$	
V_{GT}	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	\leq	1.5	V
		$T_{VJ} = -40^\circ\text{C}$	\leq	1.6	V
I_{GT}	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	\leq	100	mA
		$T_{VJ} = -40^\circ\text{C}$	\leq	200	mA
V_{GD}	$T_{VJ} = T_{VJM}$	$V_D = \frac{2}{3} V_{DRM}$	\leq	0.2	V
I_{GD}			\leq	5	mA
I_L	$T_{VJ} = 25^\circ\text{C}$; $t_p = 10 \mu\text{s}$ $I_G = 0.45 \text{ A}$; $di_G/dt = 0.45 \text{ A}/\mu\text{s}$	\leq	450	mA	
I_H	$T_{VJ} = 25^\circ\text{C}$; $V_D = 6 \text{ V}$; $R_{GK} = \infty$	\leq	200	mA	
t_{gd}	$T_{VJ} = 25^\circ\text{C}$; $V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 \text{ A}$; $di_G/dt = 0.45 \text{ A}/\mu\text{s}$	\leq	2	μs	
t_q	$T_{VJ} = T_{VJM}$; $I_T = 20 \text{ A}$, $t_p = 200 \mu\text{s}$; $di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}$; $dv/dt = 15 \text{ V}/\mu\text{s}$; $V_D = \frac{2}{3} V_{DRM}$	typ.	150	μs	
R_{thJC}	per thyristor; DC		0.92	K/W	
	per module		0.23	K/W	
R_{thJK}	per thyristor; DC		1.22	K/W	
	per module		0.31	K/W	
d_s	Creeping distance on surface		12.7	mm	
d_A	Creepage distance in air		9.4	mm	
a	Max. allowable acceleration		50	m/s^2	

Dimensions in mm (1 mm = 0.0394")

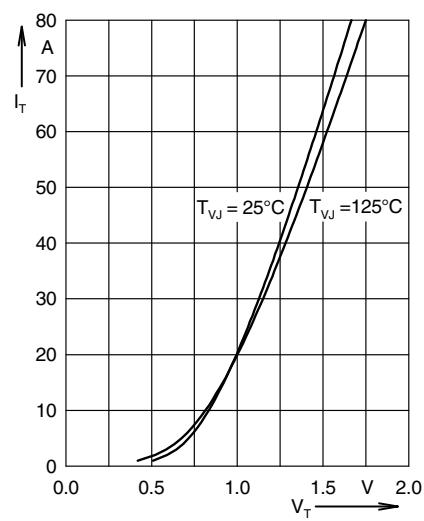
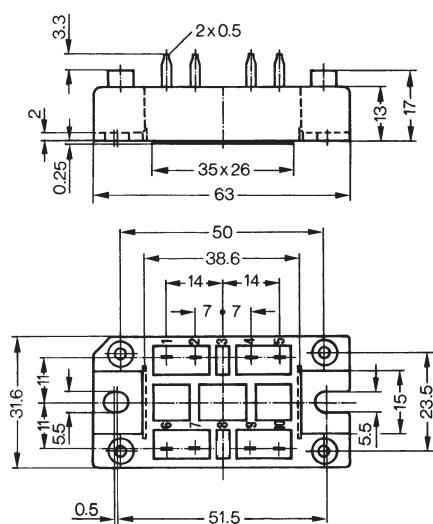


Fig. 3 Forward current vs.
voltage drop per leg

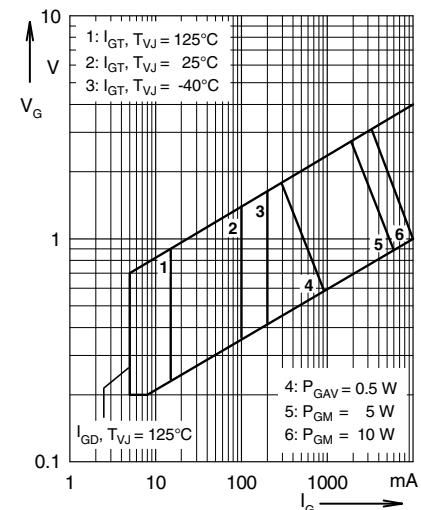


Fig. 1 Gate trigger characteristics

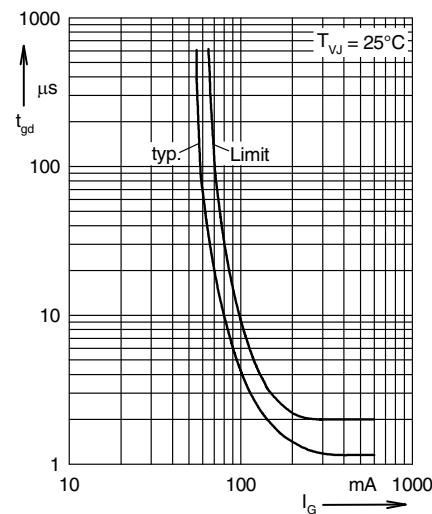


Fig. 2 Gate trigger delay time

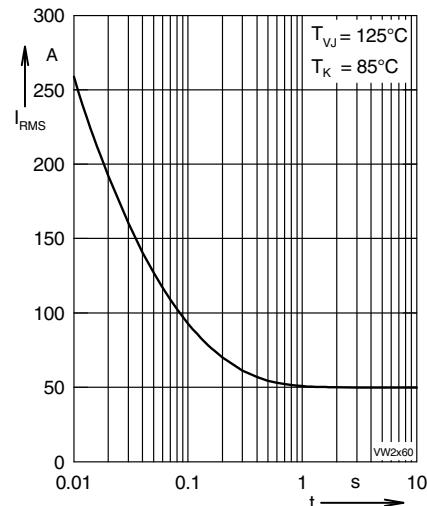


Fig. 4 Rated RMS current vs. time
(360° conduction)

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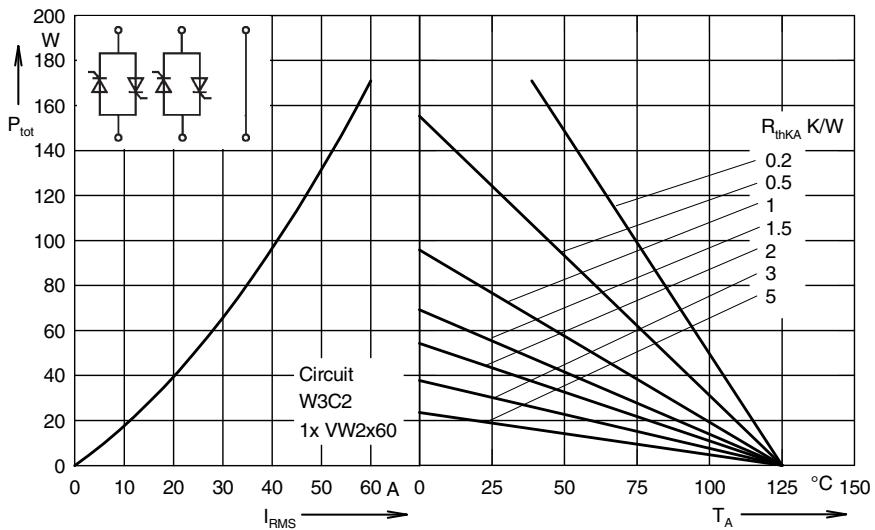


Fig. 5 Load current capability for two phase AC controller

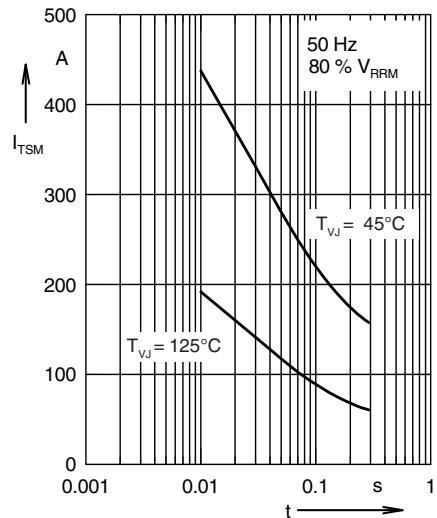


Fig. 6 Surge overload current

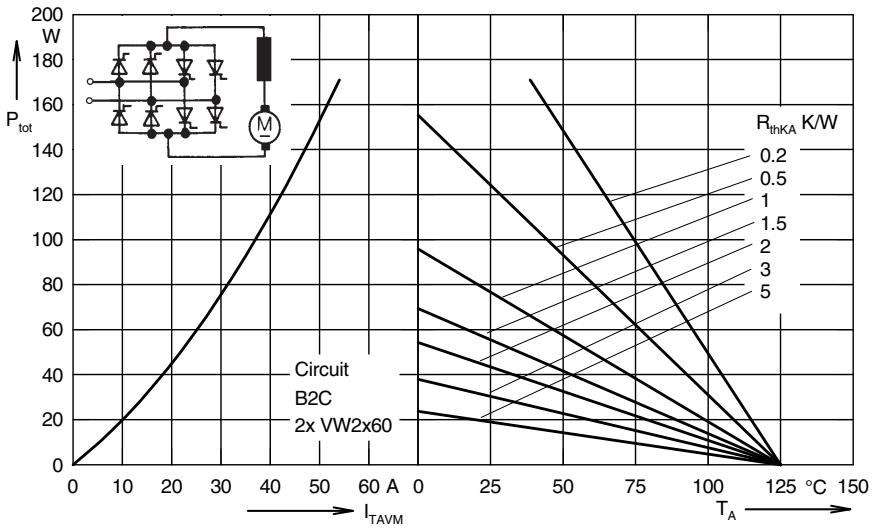


Fig. 7 Power dissipation vs. direct output current and ambient temperature cyclo converter, four quadrant operation

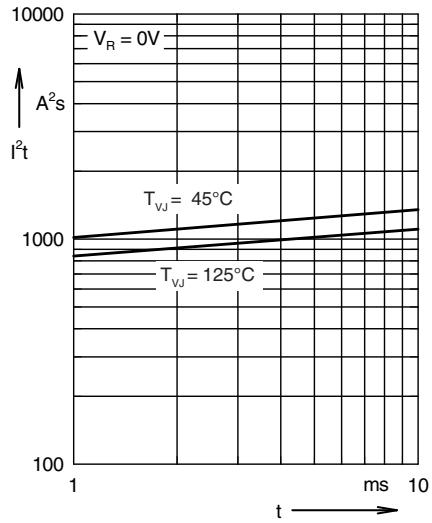


Fig. 8 I^2t vs. time (per thyristor)

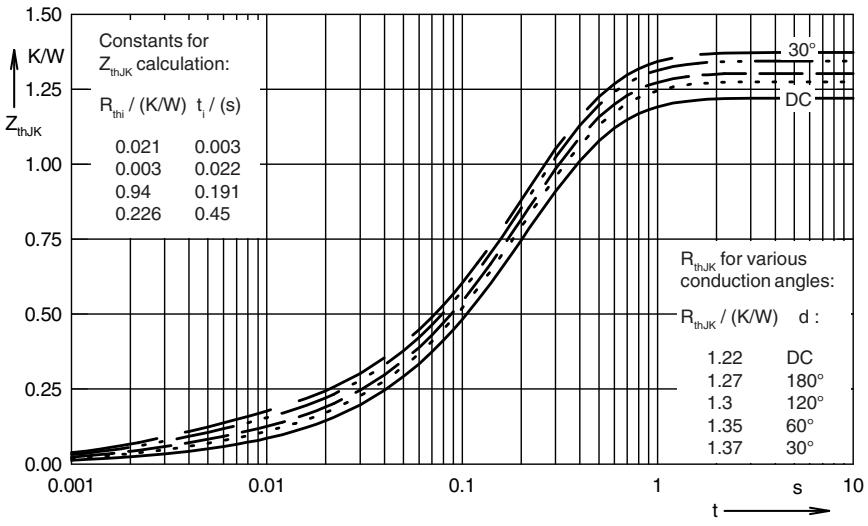


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor)

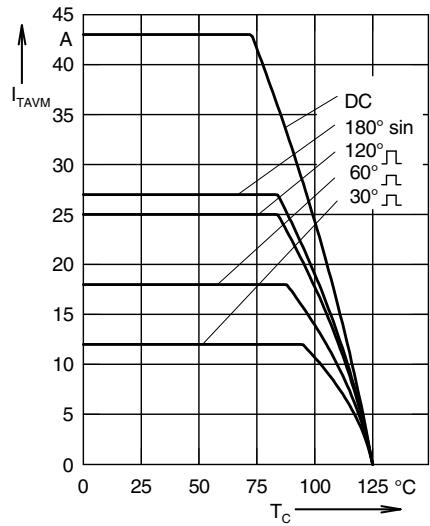


Fig. 10 Maximum forward current at case temperature
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